

Silicon PNP Power Transistor

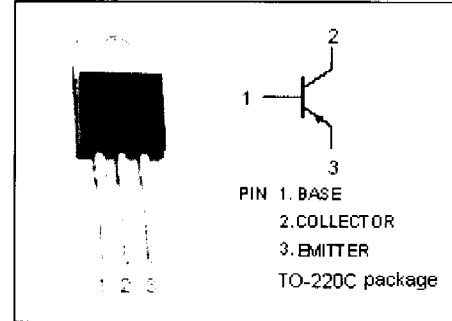
2SA1069A

DESCRIPTION

- Low Collector Saturation Voltage
- Fast Switching Speed

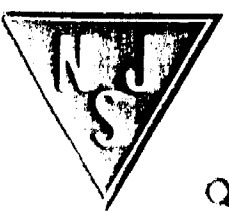
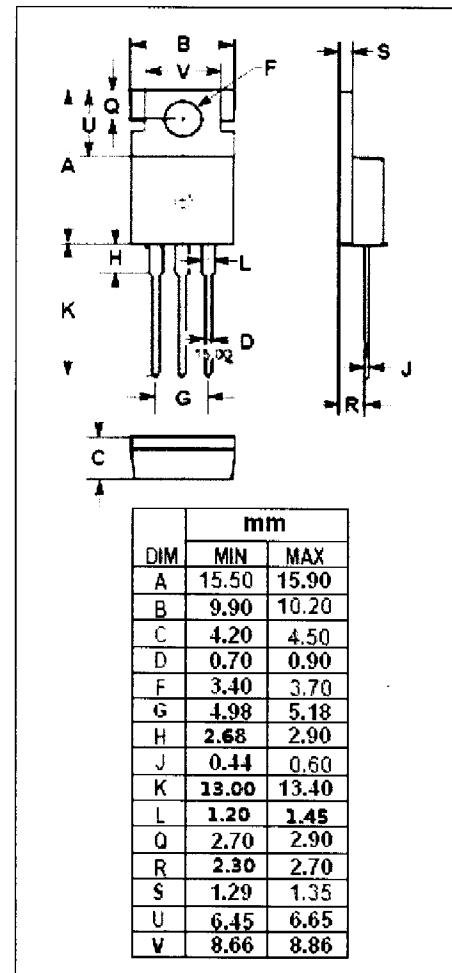
APPLICATIONS

- Designed for high-speed switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high frequency power amplifiers.



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------|
| V _{CBO} | Collector-Base Voltage | -80 | V |
| V _{CEO} | Collector-Emitter Voltage | -80 | V |
| V _{EBO} | Emitter-Base Voltage | -12 | V |
| I _C | Collector Current-Continuous | -5 | A |
| I _{CM} | Collector Current-Peak | -10 | A |
| I _B | Base Current-Continuous | -2.5 | A |
| P _C | Collector Power Dissipation @ T _a =25°C | 1.5 | W |
| | Total Power Dissipation @ T _c =25°C | 30 | |
| T _J | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature Range | -55~150 | °C |



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|------------------|--------------------------------------|---|-----|-------------|---------------|
| $V_{CE0(SUS)}$ | Collector-Emitter Sustaining Voltage | $I_C = -3.0A; I_B = -0.3A, L=1mH$ | -80 | | V |
| $V_{CEX(SUS)-1}$ | Collector-Emitter Sustaining Voltage | $I_C = -3.0A; I_{B1} = -I_{B2} = -0.3A, V_{BE(OFF)} = 5.0V, L=180\mu H, \text{clamped}$ | -80 | | V |
| $V_{CEX(SUS)-2}$ | Collector-Emitter Sustaining Voltage | $I_C = -6.0A; I_{B1} = -0.6A; I_{B2} = -0.3A, V_{BE(OFF)} = 5.0V, L=180\mu H, \text{clamped}$ | -80 | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = -3.0A; I_B = -0.3A$ | | -0.6 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = -3.0A; I_B = -0.3A$ | | -1.5 | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB} = -60V; I_E = 0$ | | -10 | μA |
| I_{CER} | Collector Cutoff Current | $V_{CE} = -80V; R_{BE} = 51\Omega, T_a = 125^\circ\text{C}$ | | -1.0 | mA |
| I_{CEX} | Collector Cutoff Current | $V_{CE} = -80V; V_{BE(off)} = -1.5V$ $V_{CE} = -80V; V_{BE(off)} = -1.5V, T_a = 125^\circ\text{C}$ | | -10 -1.0 | μA mA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB} = -5V; I_C = 0$ | | -10 | μA |
| h_{FE-1} | DC Current Gain | $I_C = -0.3A; V_{CE} = -5V$ | 40 | | |
| h_{FE-2} | DC Current Gain | $I_C = -3.0A; V_{CE} = -5V$ | 40 | 200 | |

Switching times

| | | | | | |
|-----------|--------------|--|--|-----|---------|
| t_{on} | Turn-on Time | $I_C = -3.0A, R_L = 17\Omega, I_{B1} = -I_{B2} = -0.3A, V_{CC} \approx -50V$ | | 0.5 | μs |
| t_{sig} | Storage Time | | | 2.5 | μs |
| t_f | Fall Time | | | 0.5 | μs |

◆ h_{FE-2} Classifications

| M | L | K |
|-------|--------|---------|
| 40-80 | 60-120 | 100-200 |